



TO-92 Plastic-Encapsulate Transistors

KSA642 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_D : 0.4 W ($T_{amb}=25^{\circ}C$)

Collector current

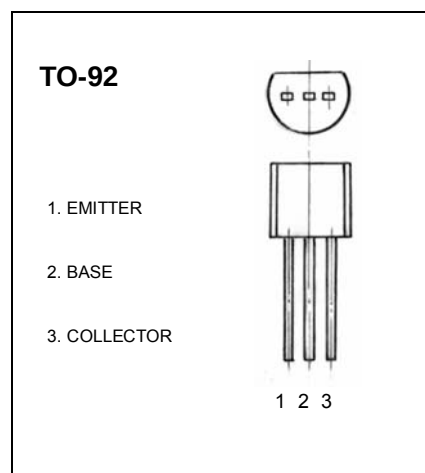
I_{CM} : -0.3 A

Collector-base voltage

$V_{(BR)CBO}$: -30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -25V, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{CB} = -3V, I_C = 0$		-0.1	μA
DC current gain *	h_{FE}	$V_{CE} = -1\text{ V}, I_C = -50\text{ mA}$	70	400	
Collector-emitter saturation voltage*	V_{CEsat}	$I_C = -0.3A, I_B = -30\text{ mA}$		-0.6	V

* Pulse Test: $p_w \leq 350\mu s$, duty cycle $\leq 2\%$.

CLASSIFICATION OF h_{FE}

Rank	O	Y	G
Range	70-140	120-240	200-400